
2SK1167, 2SK1168

Silicon N-Channel MOS FET

HITACHI

Application

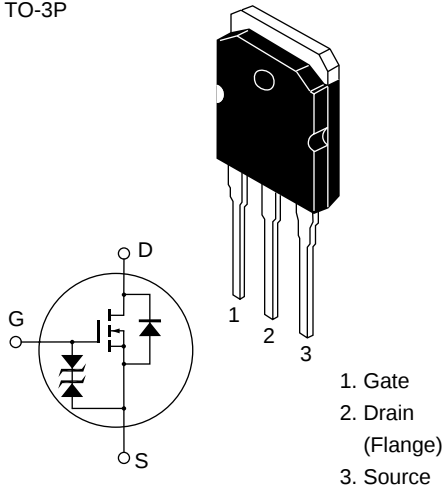
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

TO-3P



2SK1167, 2SK1168

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1167	V_{DSS}	450	V
	2SK1168		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	15	A
Drain peak current		$I_{D(pulse)}^{*1}$	60	A
Body to drain diode reverse drain current		I_{DR}	15	A
Channel dissipation		P_{ch}^{*2}	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−55 to +150	°C

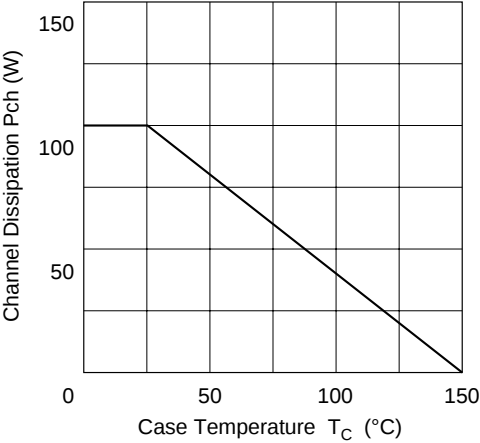
Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

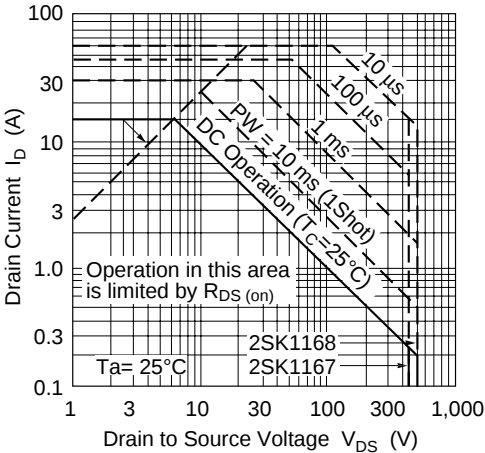
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1167 $V_{(BR)DSS}$ 2SK1168	450 500	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	2SK1167 I_{DSS} 2SK1168	—	—	250	μA	$V_{DS} = 360 \text{ V}$, $V_{GS} = 0$ $V_{DS} = 400 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	2SK1167 $R_{DS(on)}$ 2SK1168	— —	0.25 0.30	0.36 0.40	Ω	$I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	8	13	—	S	$I_D = 8 \text{ A}$, $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	2050	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$,
Output capacitance	C_{oss}	—	600	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	75	—	pF	
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}$,
Rise time	t_r	—	110	—	ns	$R_L = 3.75 \Omega$
Turn-off delay time	$t_{d(off)}$	—	150	—	ns	
Fall time	t_f	—	70	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 15 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	500	—	ns	$I_F = 15 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

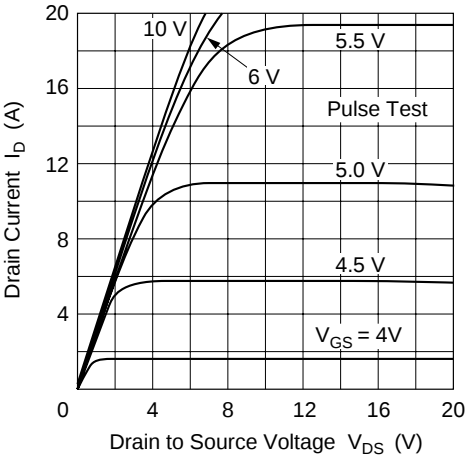
Power vs. Temperature Derating



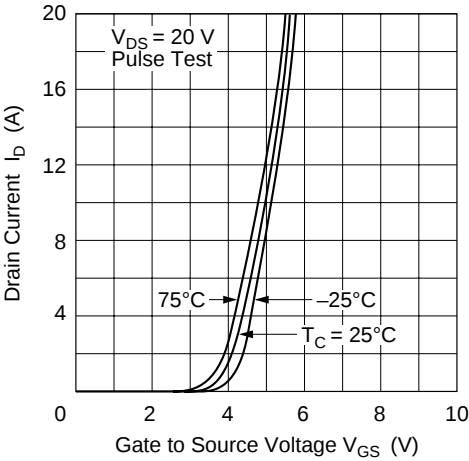
Maximum Safe Operation Area

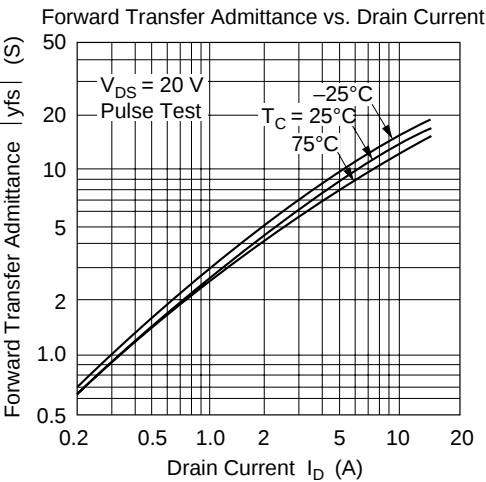
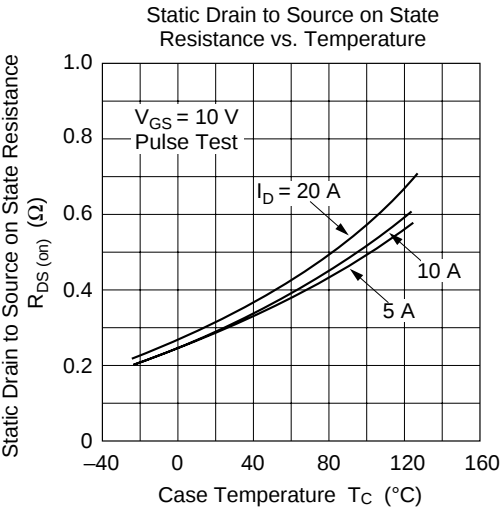
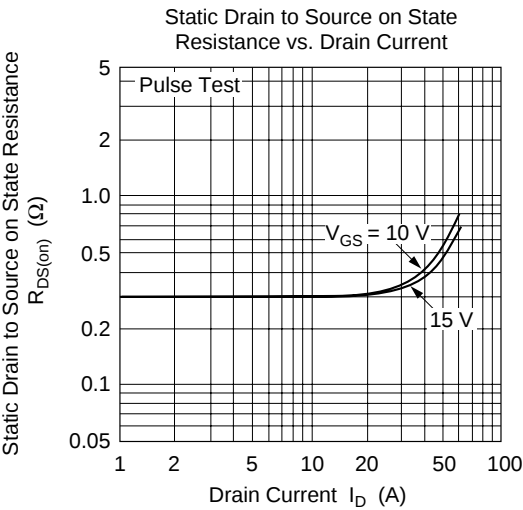
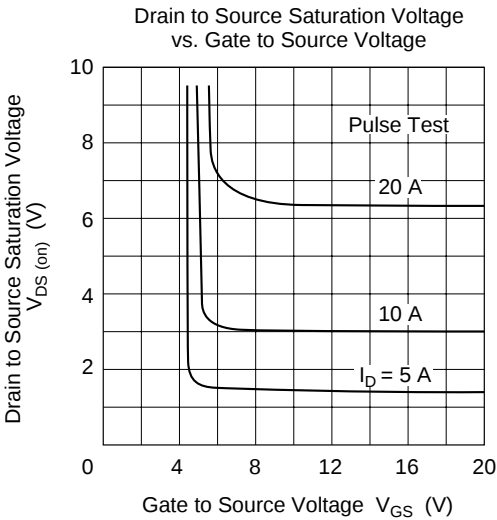


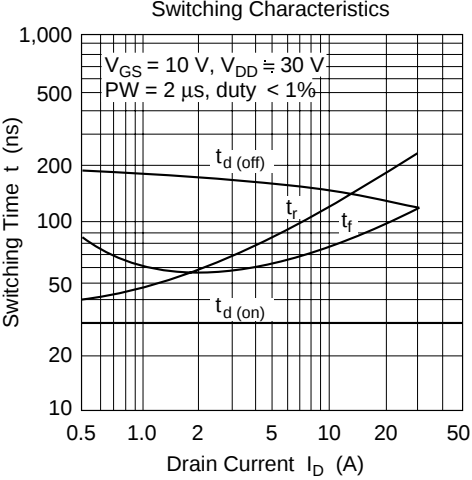
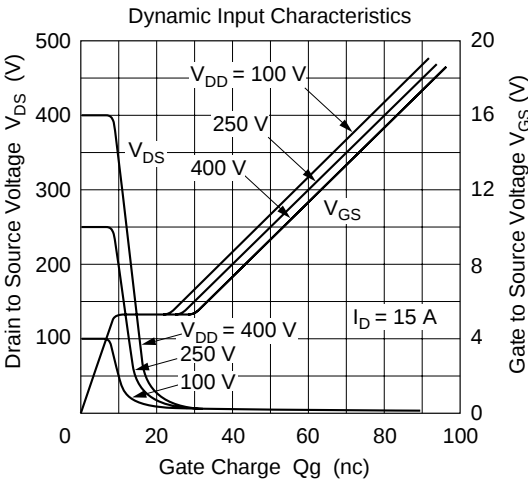
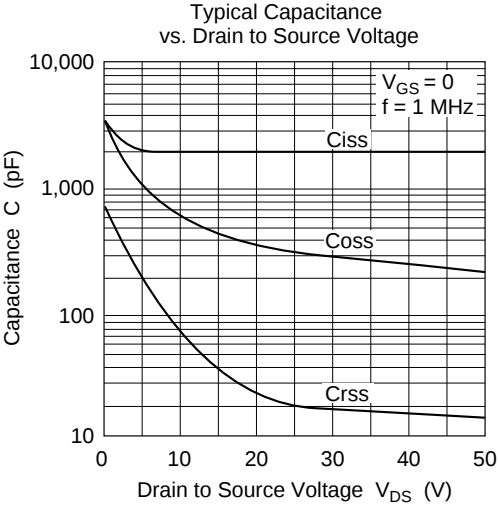
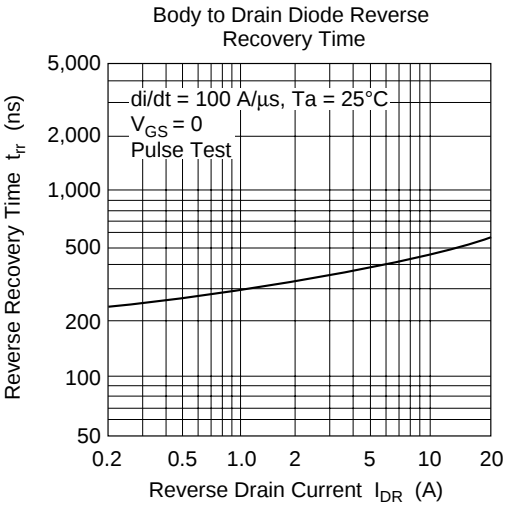
Typical Output Characteristics

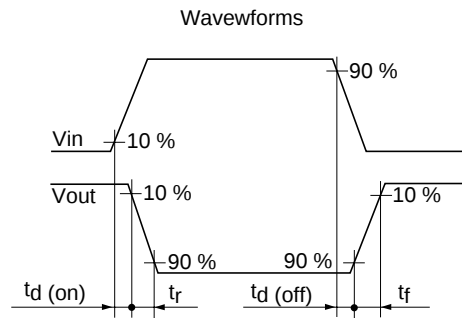
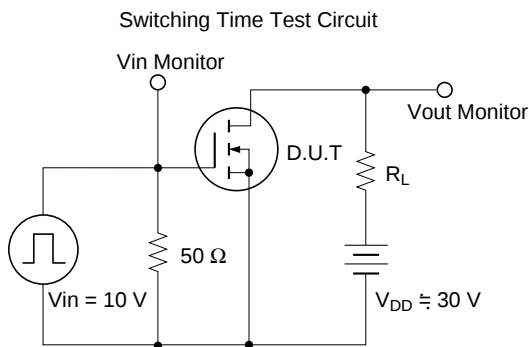
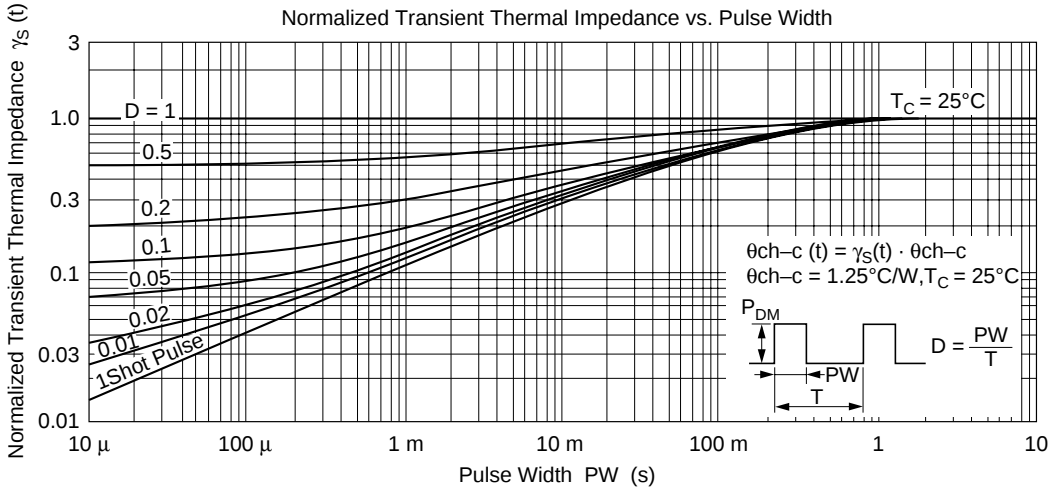
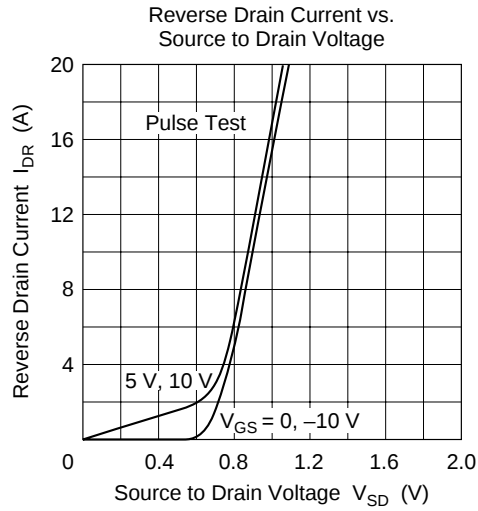


Typical Transfer Characteristics

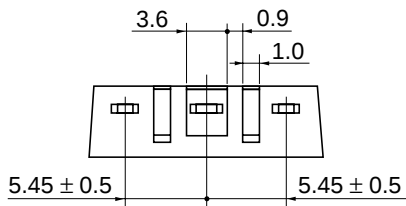
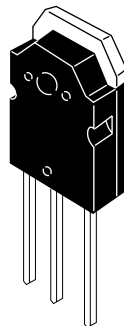
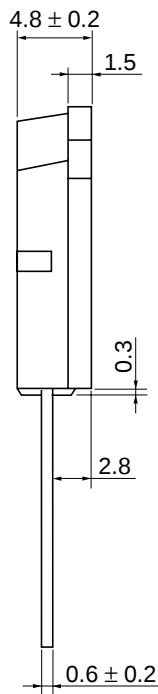
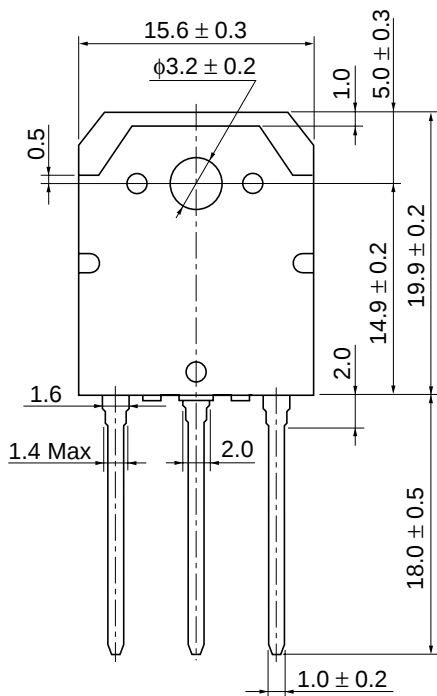








Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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